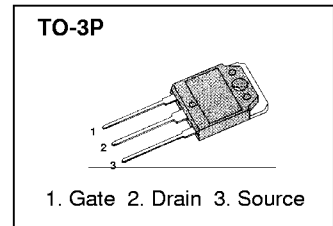


FEATURES

- Advanced New Design
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Very Low Intrinsic Capacitances
- Excellent Switching Characteristics
- Unrivalled Gate Charge: 40nC (Typ.)
- Extended Safe Operating Area
- Lower $R_{DS(ON)}$: 1.5Ω (Typ.)

$BV_{DSS} = 900V$
 $R_{DS(ON)} = 1.9\Omega$
 $I_D = 6.4A$



ABSOLUTE MAXIMUM RATINGS

Symbol	Characteristics	Value	Units
V_{DSS}	Drain-to-Source Voltage	900	V
I_D	Continuous Drain Current ($T_C = 25^\circ C$)	6.4	A
	Continuous Drain Current ($T_C = 100^\circ C$)	4.0	
I_{DM}	Drain Current-Pulsed ①	25.6	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy ②	715	mJ
I_{AR}	Avalanche Current ①	6.4	A
E_{AR}	Repetitive Avalanche Energy ①	19.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.0	V/ns
P_D	Total Power Dissipation ($T_C = 25^\circ C$)	198	W W/°C
	Linear Derating Factor	1.58	
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

THERMAL RESISTANCE

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	-	0.63	°C/W
$R_{\theta CS}$	Case-to-Sink	0.24	-	
$R_{\theta JA}$	Junction-to-Ambient	-	40	

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristics	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-Source Breakdown Voltage	900	–	–	V	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	–	0.96	–	V/ $^\circ\text{C}$	$I_D=250\mu\text{A}$, See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	3.0	–	5.0	V	$V_{DS}=5\text{V}$, $I_D=250\mu\text{A}$
I_{GSS}	Gate-Source Leakage, Forward	–	–	100	nA	$V_{GS}=30\text{V}$
	Gate-Source Leakage, Reverse	–	–	–100		$V_{GS}= -30\text{V}$
I_{DSS}	Drain-to-Source Leakage Current	–	–	10	μA	$V_{DS}=900\text{V}$
		–	–	100		$V_{DS}=720\text{V}$, $T_C=125^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	–	–	1.9	Ω	$V_{GS}=10\text{V}$, $I_D=3.2\text{A}$ ④
g_{fs}	Forward Transconductance	–	5.7	–	S	$V_{DS}=50\text{V}$, $I_D=3.2\text{A}$ ④
C_{iss}	Input Capacitance	–	1440	1880	pF	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$ $f=1\text{MHz}$ See Fig 5
C_{oss}	Output Capacitance	–	140	185		
C_{rss}	Reverse Transfer Capacitance	–	17	23		
$t_{d(on)}$	Turn-On Delay Time	–	35	80	ns	$V_{DD}=450\text{V}$, $I_D=5.8\text{A}$ $R_G=50\Omega$ See Fig 13 ④ ⑤
t_r	Rise Time	–	80	170		
$t_{d(off)}$	Turn-Off Delay Time	–	95	200		
t_f	Fall Time	–	55	120		
Q_g	Total Gate Charge	–	40	52	nC	$V_{DS}=720\text{V}$, $V_{GS}=10\text{V}$ $I_D=5.8\text{A}$ See Fig 6 & Fig 12 ④ ⑤
Q_{gs}	Gate-Source Charge	–	8.5	–		
Q_{gd}	Gate-Drain (Miller) Charge	–	20	–		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristics	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current	–	–	6.4	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	–	–	25.6		
V_{SD}	Diode Forward Voltage ④	–	–	1.4	V	$T_J=25^\circ\text{C}$, $I_S=6.4\text{A}$, $V_{GS}=0\text{V}$
t_{rr}	Reverse Recovery Time	–	400	–	ns	$T_J=25^\circ\text{C}$, $I_F=5.8\text{A}$, $V_{DD}=720\text{V}$ $di_F/dt=100\text{A}/\mu\text{s}$ ④
Q_{rr}	Reverse Recovery Charge	–	4.3	–	μC	

Notes:

- ① Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- ② $L=33\text{mH}$, $I_{AS}=6.4\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
- ③ $I_{SD} \leq 5.8\text{A}$, $di/dt \leq 400\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$
- ④ Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
- ⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

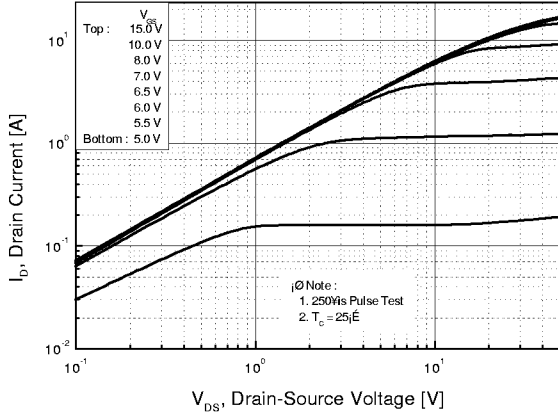


Fig 2. Transfer Characteristics

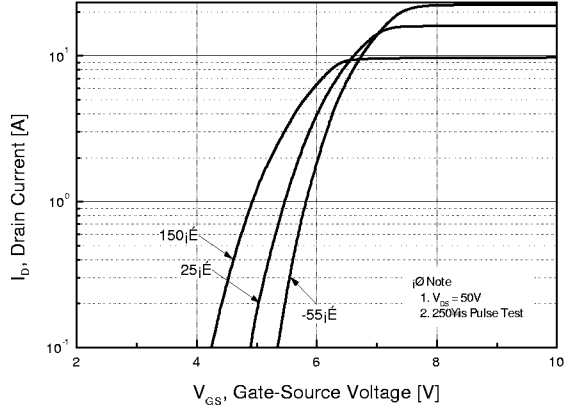


Fig 3. On-Resistance vs. Drain Current

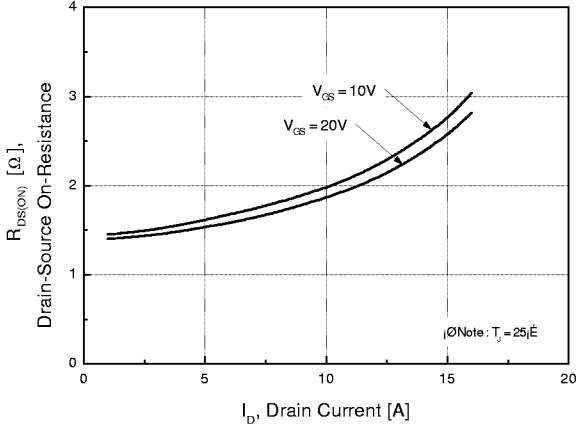


Fig 4. Source-Drain Diode Forward Voltage

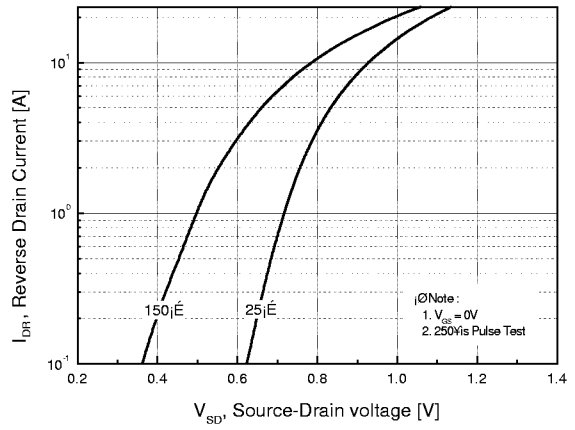


Fig 5. Capacitance vs. Drain-Source Voltage

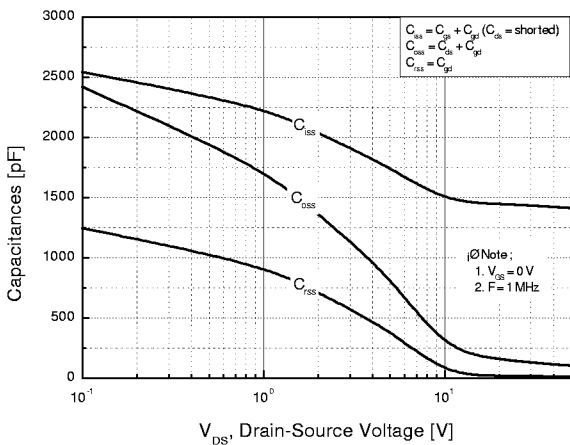


Fig 6. Gate Charge vs. Gate-Source Voltage

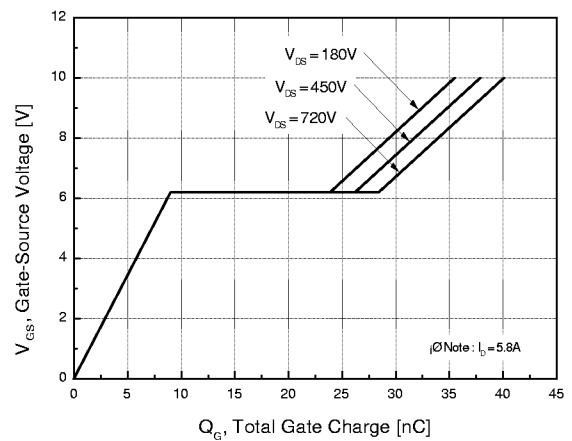


Fig 7. Breakdown Voltage vs. Temperature

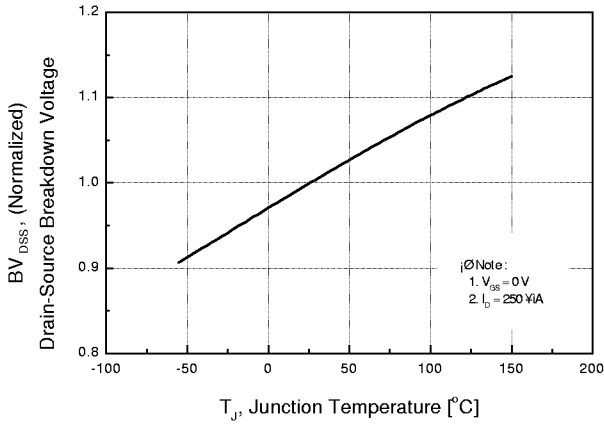


Fig 8. On-Resistance vs. Temperature

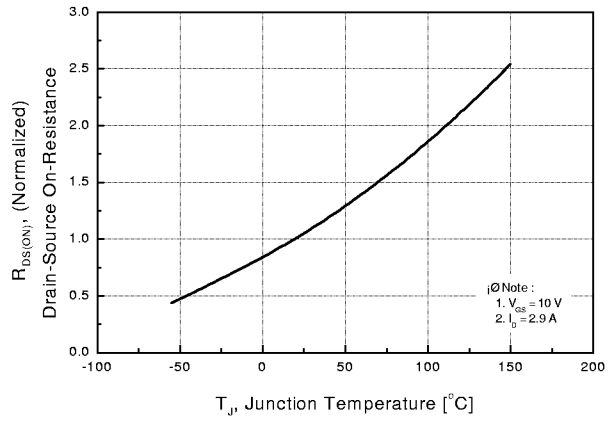


Fig 9. Max. Safe Operating Area

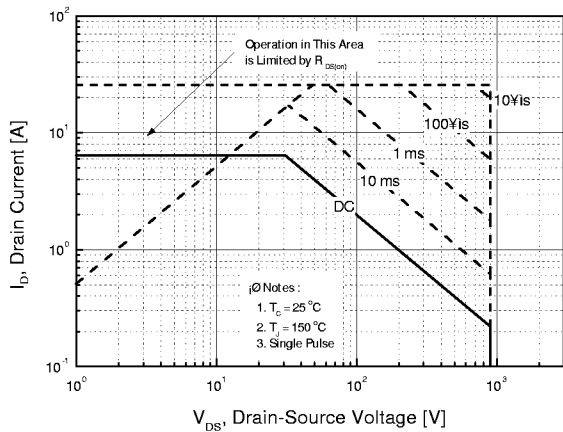


Fig 10. Max. Drain Current vs. Case Temperature

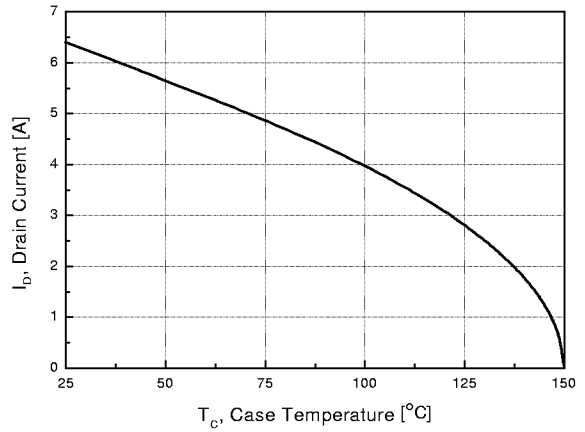


Fig 11. Thermal Response

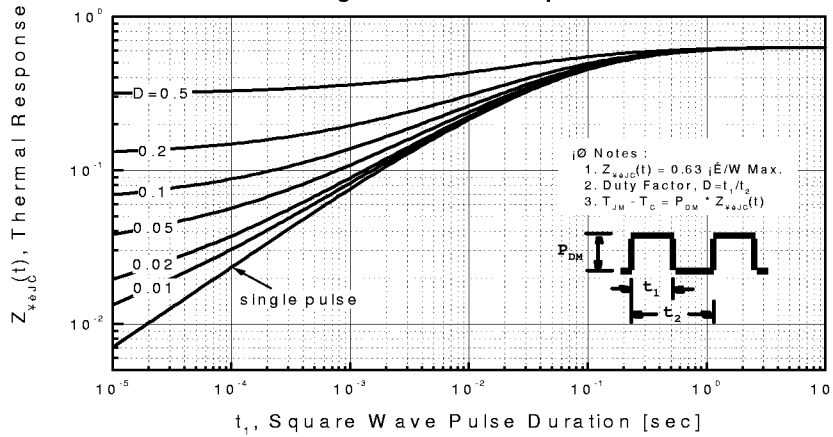


Fig 12. Gate Charge Test Circuit & Waveform

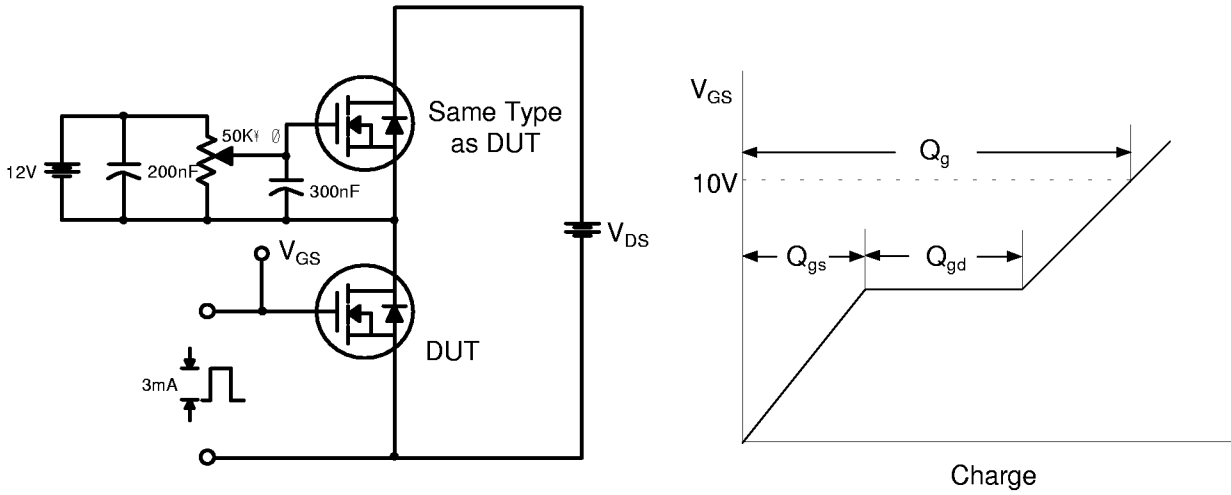


Fig 13. Resistive Switching Test Circuit & Waveforms

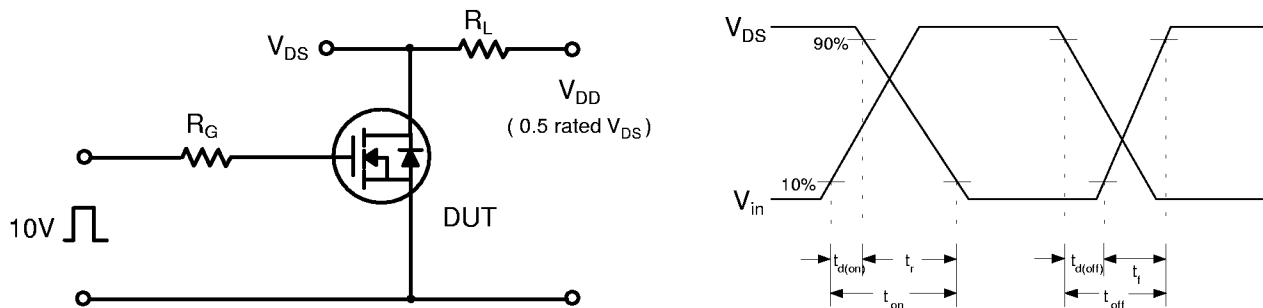


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

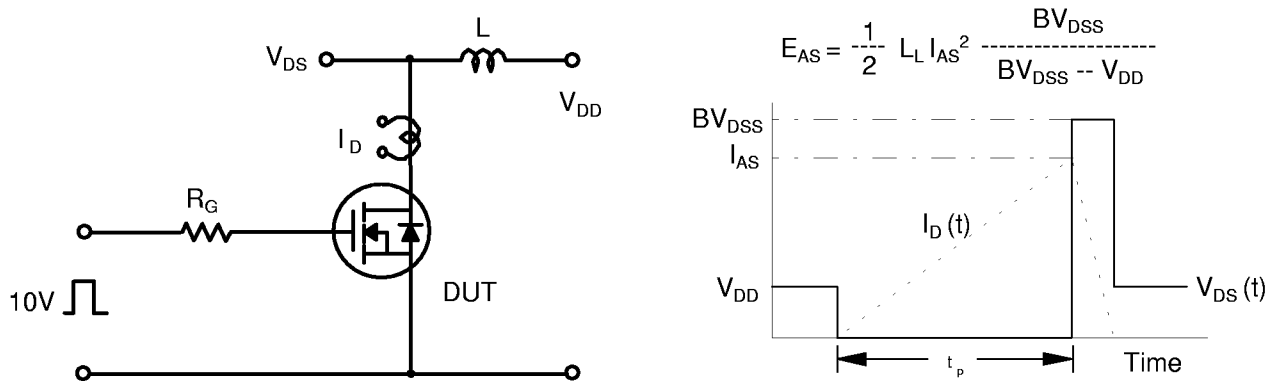
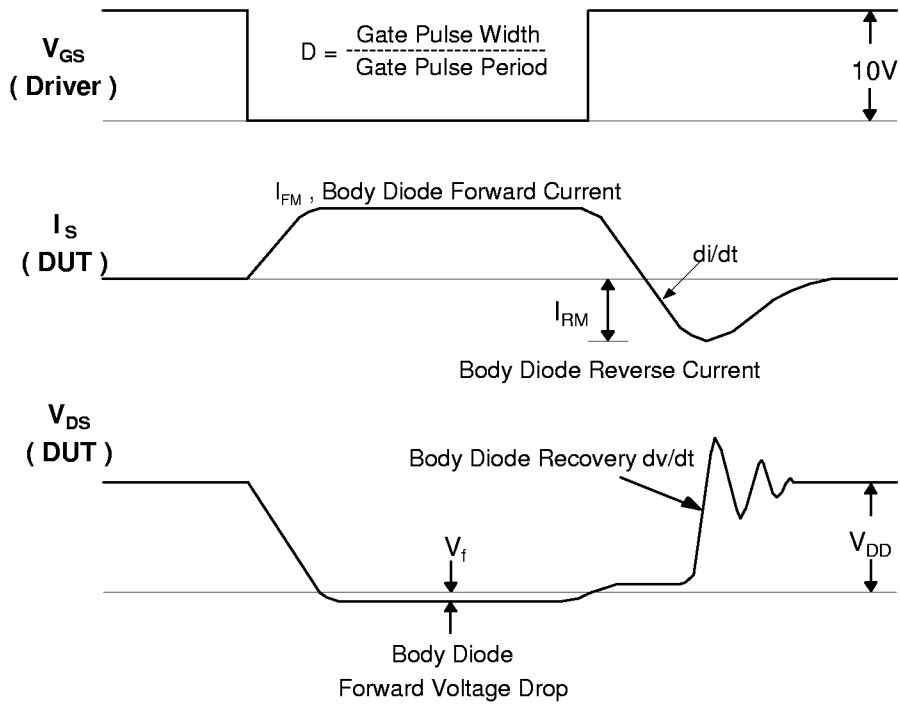
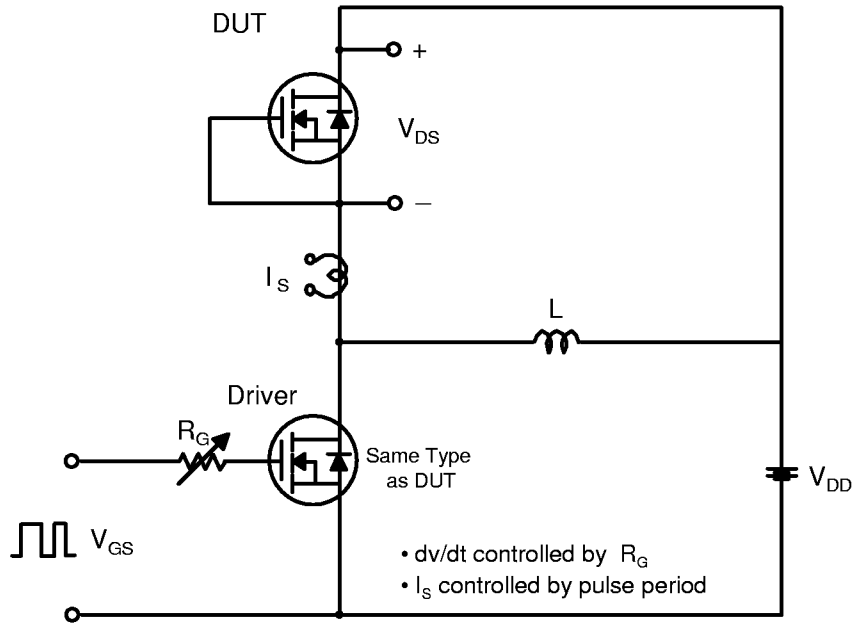
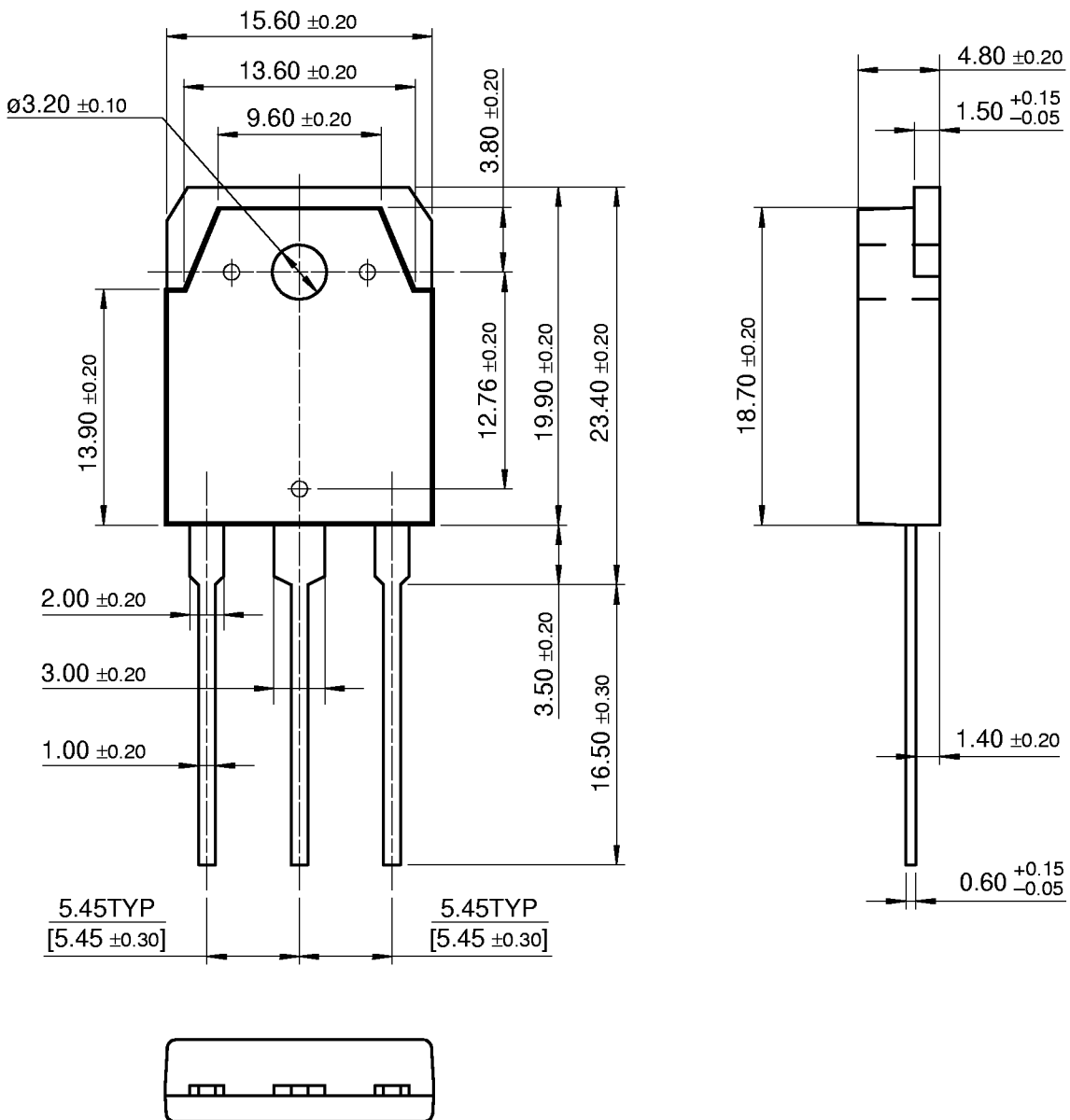


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



TO-3P Package Dimensions

TO-3P (FS PKG CODE AF)



Dimensions in Millimeters
September 1999, Rev B